Center gate International standard case TO-94 (TO-209AC)

- · Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- · Hermetic glass-metal case with ceramic insulator (Glass-metal seal over 1200 V)
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

FEATURES

MAJOR RATINGS AND CHARACTERISTICS							
PARAMETER	TEST CONDITIONS	VALUES	UNITS				
1		110	A				
I _{T(AV)}	T _C	90	°C				
I _{T(RMS)}		175					
I _{TSM}	50 Hz	2700	A				
	60 Hz	2830					
l ² t	50 Hz	36.4	– kA ² s				
I-t	60 Hz	33.2	KA2S				
V _{DRM} /V _{RRM}		400 to 1600	V				
tq	Typical	100	μs				
TJ		-40 to +125	°C				

ELECTRICAL SPECIFICATIONS

VOLTAGE R	ATINGS				
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$I_{DRM}/I_{RRM} MAXIMUM AT T_J = T_J MAXIMUM mA$	
	04	400	500		
VS-ST110S	08	800	900	20	
VS-S11105	12	1200	1300	20	
	16	1600	1700		

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Phase Control Thyristors (Stud Version), 110 A





PRIMARY CHARACTERISTICS							
I _{T(AV)}	110 A						
V _{DRM} /V _{RRM}	400 V, 800 V, 1200 V, 1600 V						
V _{TM}	1.52 V						
I _{GT}	150 mA						
TJ	-40 °C to +125 °C						
Package	TO-94 (TO-209AC)						
Circuit configuration	Single SCR						

VS-ST110SPbF Series

Vishay Semiconductors





Document Number: 94393

VS-ST110SPbF Series



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ABSOLUTE MAXIMUM RATINGS	5					
PARAMETER	SYMBOL		VALUES	UNITS		
Maximum average on-state current at case temperature	I _{T(AV)}	180° condu	180° conduction, half sine wave		110 90	A °C
Maximum RMS on-state current	I _{T(RMS)}	DC at 85 °C	case temperat	ure	175	
	(-)	t = 10 ms	No voltage		2700	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		2830	А
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		2270	
		t = 8.3 ms	reapplied	Sinusoidal half wave, initial T _J = T _J maximum	2380	
		t = 10 ms	No voltage		36.4	kA ² s
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied		33.2	
Maximum - t for fusing	1-1	t = 10 ms 100 % V _{RRM}		25.8	NA-5	
		t = 8.3 ms	reapplied		23.5	
Maximum I ² √t for fusing	l²√t	t = 0.1 to 10) ms, no voltage	e reapplied	364	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x \ I_{T(AV)} < I < \pi \ x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.90	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$), $T_J = T_J$ maxin	num	0.92	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		1.79	mΩ	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$		1.81	1115.2	
Maximum on-state voltage	V _{TM}	I _{pk} = 350 A,	$T_J = T_J$ maximu	ım, t _p = 10 ms sine pulse	1.52	V
Maximum holding current	Ι _Η	T 25 °C	anodo supply 1	2 V resistive load	600	m۸
Typical latching current	١L	$1_{\rm J} = 25$ C,	anoue supply 1		1000	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq 1 \; \mu s$ $T_J = T_J$ maximum, anode voltage $\leq 80 \; \% \; V_{DRM}$	500	A/µs
Typical delay time t _d		Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	2.0	110
Typical turn-off time	tq	I_{TM} = 100 A, T_J = T_J maximum, dl/dt = 10 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	20	mA



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TR			

TRIGGERING								
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES			
FANAMEIEN				TYP.	MAX.			
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	$t_p \le 5 ms$		5	W		
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50		1	vv		
Maximum peak positive gate current	I _{GM}			2	.0	А		
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms		2	0	v		
Maximum peak negative gate voltage	- V _{GM}		5.0		.0	v		
		T _J = -40 °C		180	-			
DC gate current required to trigger	I _{GT}	T _J = 25 °C	Maximum required gate trigger	90	150	mA		
		T _J = 125 °C	current/voltage are the lowest	40	-			
		T _J = -40 °C	value which will trigger all units	2.9	-			
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	6 V anode to cathode applied	1.8	3.0	V		
		T _J = 125 °C		1.2	-			
DC gate current not to trigger	I _{GD}		Maximum gate current/voltage	1	0	mA		
DC gate voltage not to trigger	V _{GD}	T _J = T _J maximum	not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		v		

PARAMETER	SYMBOL TEST CONDITIONS		VALUES	UNITS	
Maximum operating junction temperature range	on TJ		-40 to 125	°C	
Maximum storage temperature range	T _{Stg}		-40 to 150		
Maximum thermal resistance, junction to case	R _{thJC}	R _{thJC} DC operation		12.0.07	
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased 0.08		K/W	
		Non-lubricated threads	15.5 (137)	Nm	
Mounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf · in)	
Approximate weight			130	g	
Case style		See dimensions - link at the end of datasheet	end of datasheet TO-94 (TO-209A		

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS				
180°	0.035	0.025						
120°	0.041	0.042		K/W				
90°	0.052	0.056	$T_J = T_J maximum$					
60°	0.076	0.079						
30°	0.126	0.127						

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

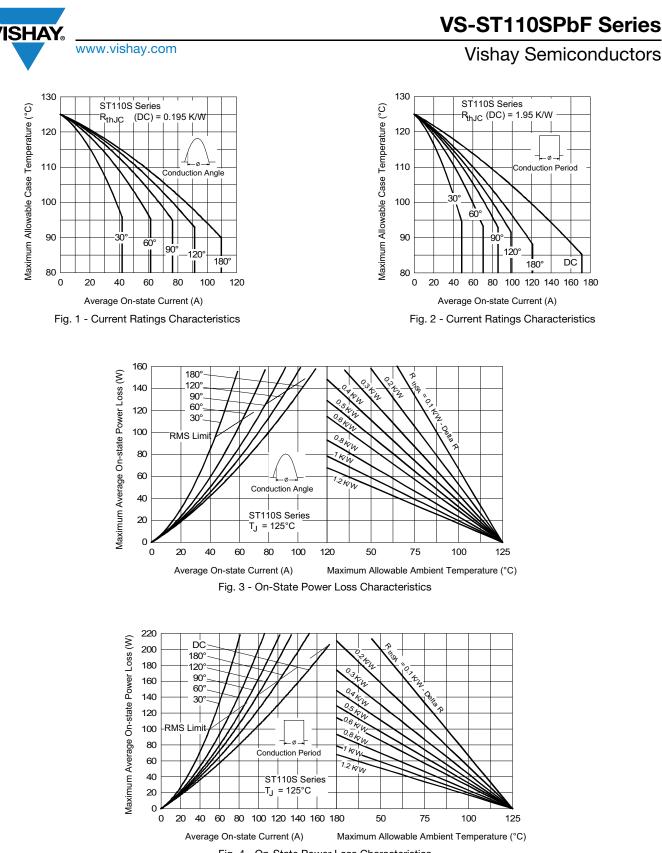
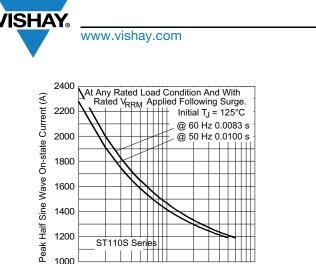


Fig. 4 - On-State Power Loss Characteristics

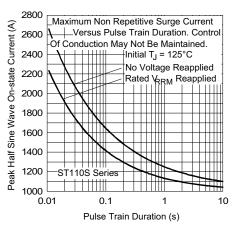


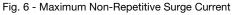
1600 1400 1200 ST110S Series 1000 10 100 1

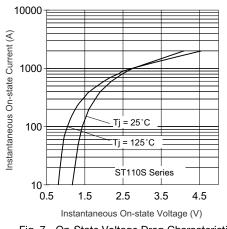
Number Of Equal Amplitude Half Cycle Current Pulses (N)

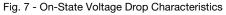
Fig. 5 - Maximum Non-Repetitive Surge Current

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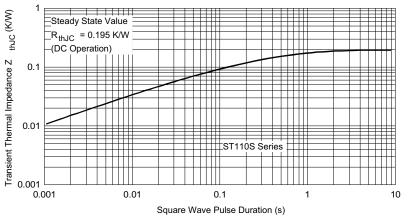
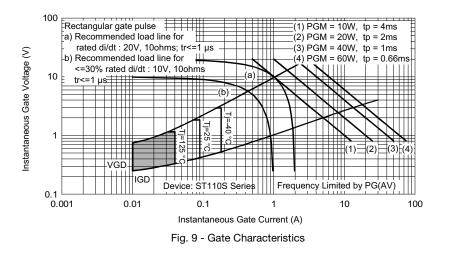


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic

VS-ST110SPbF Series

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ORDERING INFORMATION TABLE

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SHA

Device code	VS-	ST	11	0	s	16	Р	0	v	L	PbF
		(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)	(10)	(11)
		U	U	C	C	U	U	U	U	Ŭ	U
	1			nicondu	ctors pr	oduct					
		-	ristor								
	3		ential p		-						
	뜨	- 0 =	conver	er grad	e						
	-	- S=	compre	ession b	onding	stud					
	-	- Vol	tage coo	de x 100	$0 = V_{RRN}$	1 (see V	oltage F	Ratings	table)		
	7.	- P=	stud ba	ase 20U	NF threa	ads					
	8	- 0 =	eyelet t	erminals	s (gate a	ind auxi	iliary ca	thode le	eads)		
		1 =	fast-on	termina	ls (gate	and aux	kiliary c	athode	leads)		
		2 =	flag terr	minals (f	or catho	ode and	gate te	erminals)		
	9 -	• \	= glass	-metal s	seal (onl	y up to	1200 V))			
		• N	one = c	eramic I	nousing	(over 12	200 V)				
	10	- Cri	ical dV/	dt:							
		• N	one = 5	00 V/µs	(standa	rd value	e)				
		۰L	= 1000	V/µs (sp	pecial se	election))				
	11	- No	ne = sta	ndard p	roductio	on					
		- Pb	F = lead	(Pb)-fre	e						

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95078				

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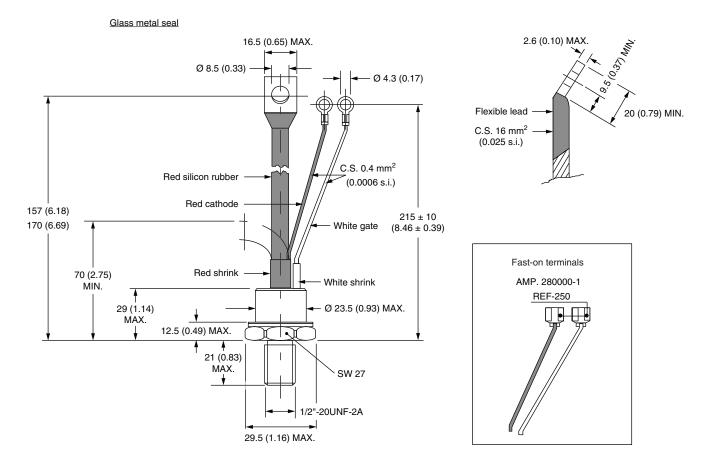
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TO-209AC (TO-94) for ST110S Series

DIMENSIONS in millimeters (inches)

SHA



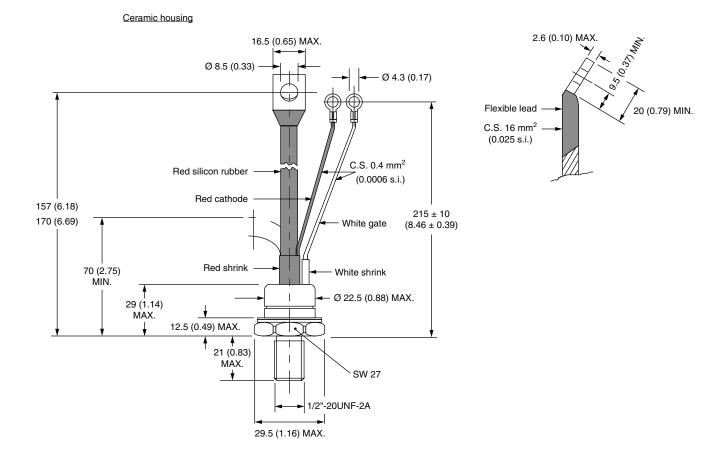
Outline Dimensions

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TO-209AC (TO-94) for ST110S Series



DIMENSIONS in millimeters (inches)





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 TT104N12KOF-A
 TT104N12KOF-K
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 TT162N16KOF-K
 TT330N16AOF
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 VS-16RIA100

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 TT251N16KOF-K
 VS

 22RIA100
 VS-16RIA40
 CR02AM-8#F00
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 GA301A
 VS-ST110S16P0
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